# ST 2SB772S

## **PNP Silicon Epitaxial Transistor**

Medium Power Low Voltage Transistor

The transistor is subdivided into three groups Q, P and E, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit	
Collector-Base Voltage	-V <sub>CBO</sub>	40	V	
Collector-Emitter Voltage	-V <sub>CEO</sub>	30	V	
Emitter-Base Voltage	-V <sub>EBO</sub>	5	V	
Collector Current	-I <sub>C</sub>	3	A	
Peak Collector Current	-I <sub>CM</sub>	7	А	
Base Current	-I <sub>B</sub>	600	mA	
Collector Dissipation	P <sub>tot</sub>	500	mW	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	T <sub>S</sub>	- 55 to + 150	°C	

## Characteristics ( $T_a = 25 \circ C$ )

Parameter		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $-V_{CE} = 2 V$ , $-I_C = 1 A$ Current Gain Group	Q	h <sub>FE</sub>	100	-	200	-
	P E	h <sub>FE</sub>	160	-	320	-
at $-V_{CE} = 2 V$ , $-I_{C} = 20 mA$	C	h <sub>FE</sub> h <sub>FE</sub>	200 30	-	400 -	-
Collector Cutoff Current at $-V_{CB} = 30 \text{ V}$		-I <sub>CBO</sub>	-	-	1	μA
Emitter Cutoff Current at $-V_{EB} = 3 V$		-I <sub>EBO</sub>	-	-	1	μA
Collector-Emitter Saturation Voltage at $-I_C = 2 A$ , $-I_B = 200 mA$		-V <sub>CE(sat)</sub>	-	-	0.5	V
Base-Emitter Saturation Voltage at $-I_{C}$ = 2 A, $-I_{B}$ = 200 mA		-V <sub>BE(sat)</sub>	-	-	2	V
Current Gain Bandwidth Product at $-V_{CE} = 5 V$ , $-I_C = 0.1 A$		f⊤	-	80	-	MHz
Output Capacitance at $-V_{CB} = 10 \text{ V}, \text{ f} = 1 \text{ MHz}$		C <sub>ob</sub>	-	45	-	pF

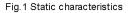


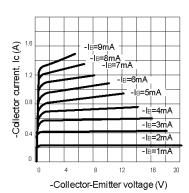
SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

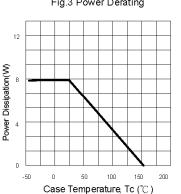


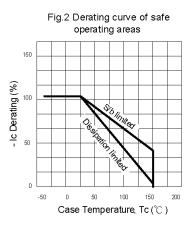
Dated : 04/10/2006

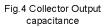












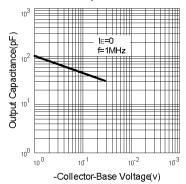


Fig.5 Current gainbandwidth product 10<sup>3</sup> Ourrent gain-bandwidth product, f⊤(MHz) VCE=5V 10<sup>2</sup> =8mA 10 10<sup>0</sup> 10<sup>-2</sup> 10-1 10 0 10

Fig.6 Safe Operating Area

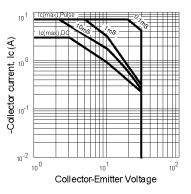
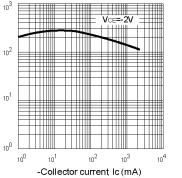
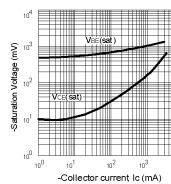


Fig.8 Saturation Voltage



DC current Gain, HFE

Collector current, Ic (A) Fig.7 DC current gain





### SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company

listed on the Hong Kong Stock Exchange, Stock Code: 724)



10



Dated : 04/10/2006